



#### 100V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> T <sub>C</sub> = +25°C
100V	13.5mΩ @ V <sub>GS</sub> = 10V	42A
	18mΩ @ V <sub>GS</sub> = 6.0V	36A

# **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

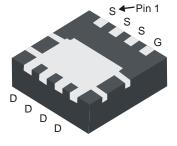
- · Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

#### **Features and Benefits**

- Low R<sub>DS(ON)</sub> Ensures On State Losses Are Minimized
- Excellent Q<sub>gd x</sub> R<sub>DS (ON)</sub> Product (FOM)
- Advanced Technology for DC/DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% UIS (Avalanche) Rated
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

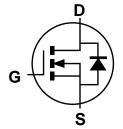
- Case: POWERDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)



Bottom View



Top View



**Equivalent Circuit** 

### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMT10H015LFG-7	POWERDI®3333-8	2,000/Tape & Reel
DMT10H015LFG-13	POWERDI®3333-8	3,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



S1H = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 15 = 2015) WW = Week Code (01 to 53)



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		$V_{DSS}$	100	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note EV) 40V	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	10 8.0	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	42 26	А
Maximum Continuous Body Diode Forward Current (Note 5)		Is	1.5	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	75	Α
Avalanche Current (L = 3mH)		I <sub>AS</sub>	7.5	A
Avalanche Energy (L = 3mH)		E <sub>AS</sub>	85	mJ

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

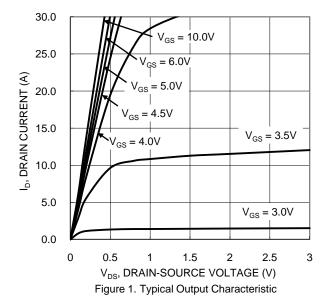
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	$P_{D}$	2.0	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ heta JA}$	61	°C/W
Total Power Dissipation	T <sub>C</sub> = +25°C	P <sub>D</sub>	35	W
Thermal Resistance, Junction to Case		$R_{ hetaJC}$	3.5	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	1	_	٧	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	1		1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	1	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.4	2.0	3.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		-	10.8	13.5	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Dialit-Source Off-Resistance	R <sub>DS(ON)</sub>	1	13.3	18	11122	$V_{GS} = 6.0V, I_D = 20A$	
Diode Forward Voltage	$V_{SD}$	1	0.9	1.3	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C <sub>iss</sub>	1	1,871	_		V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	Coss	1	261	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	1	6.9	_			
Gate Resistance	R <sub>G</sub>	1	0.75	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	1	33.3	_			
Gate-Source Charge	Q <sub>gs</sub>	1	6.9	_	nC	$V_{DD} = 50V, I_D = 10A,$ $V_{GS} = 10V$	
Gate-Drain Charge	$Q_{gd}$		5.1	_		VGS = 10V	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6.5	_		$V_{DD} = 50V, V_{GS} = 10V,$ $I_{D} = 10A, R_{G} = 6\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	7.0	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	19.7	_	ns		
Turn-Off Fall Time	t <sub>F</sub>		8.1	_			
Reverse Recovery Time	t <sub>RR</sub>	_	37.9	_	ns	I <sub>F</sub> = 10A, di/dt = 100A/μs	
Reverse Recovery Charge	$Q_{RR}$	_	51.9	_	nC	1F = 10A, αί/αι = 100A/μS	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.6. Short duration pulse test used to minimize self-heating effect.7. Guaranteed by design. Not subject to product testing.





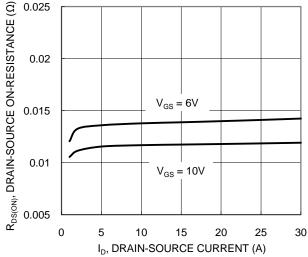


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

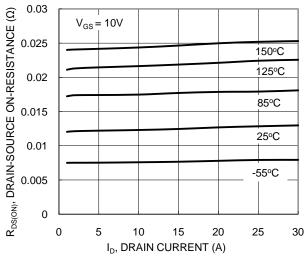
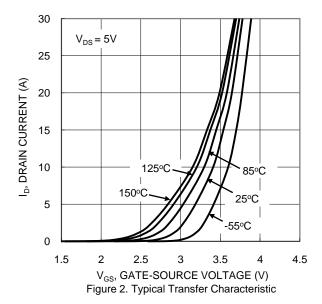


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



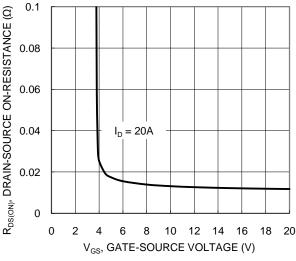


Figure 4. Typical Transfer Characteristic

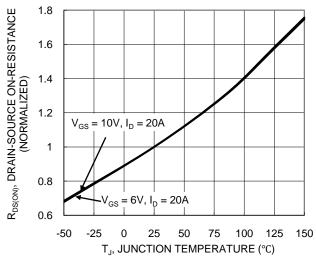


Figure 6. On-Resistance Variation with Junction Temperature



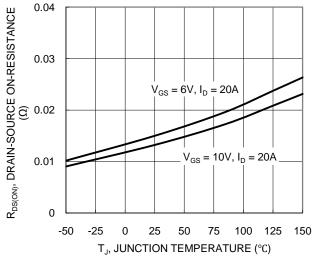


Figure 7. On-Resistance Variation with Junction Temperature

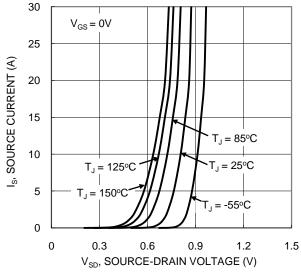


Figure 9. Diode Forward Voltage vs. Current

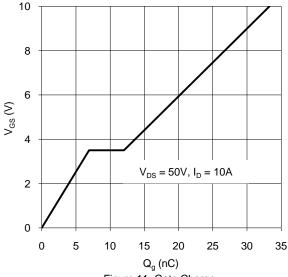


Figure 11. Gate Charge

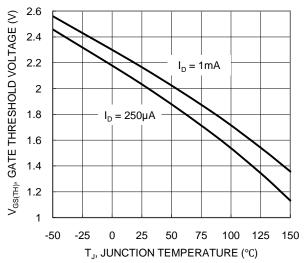
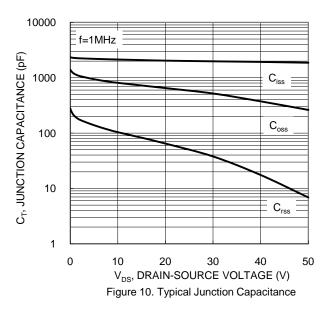


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R<sub>DS(ON)</sub> Limited 100 ID, DRAIN CURRENT (A) 10 1 ∰ P<sub>w</sub> 0.1 T<sub>C</sub> = 25 °C Single Pulse 0.01 DUT on 1\*MRP Board DC  $V_{GS} = 10V$ 0.001 0.01 10 100 1000 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



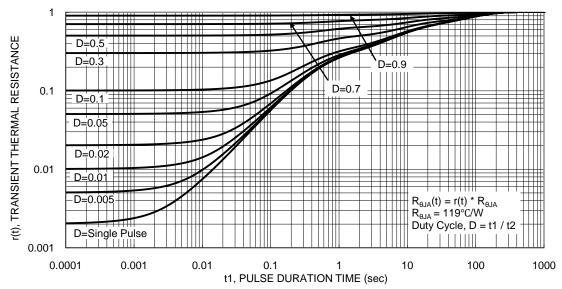
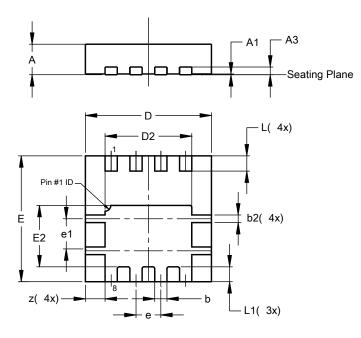


Figure 13. Transient Thermal Resistance



### **Package Outline Dimensions**

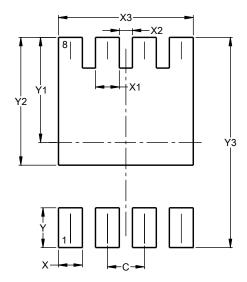
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



POWERDI®3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	_	_	0.203		
b	0.27	0.37	0.32		
b2	_	_	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
е	1	-	0.65		
e1	0.79	0.89	0.84		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)	
С	0.650	
X	0.420	
X1	0.420	
X2	0.230	
Х3	2.370	
Υ	0.700	
Y1	1.850	
Y2	2.250	
Y3	3.700	



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